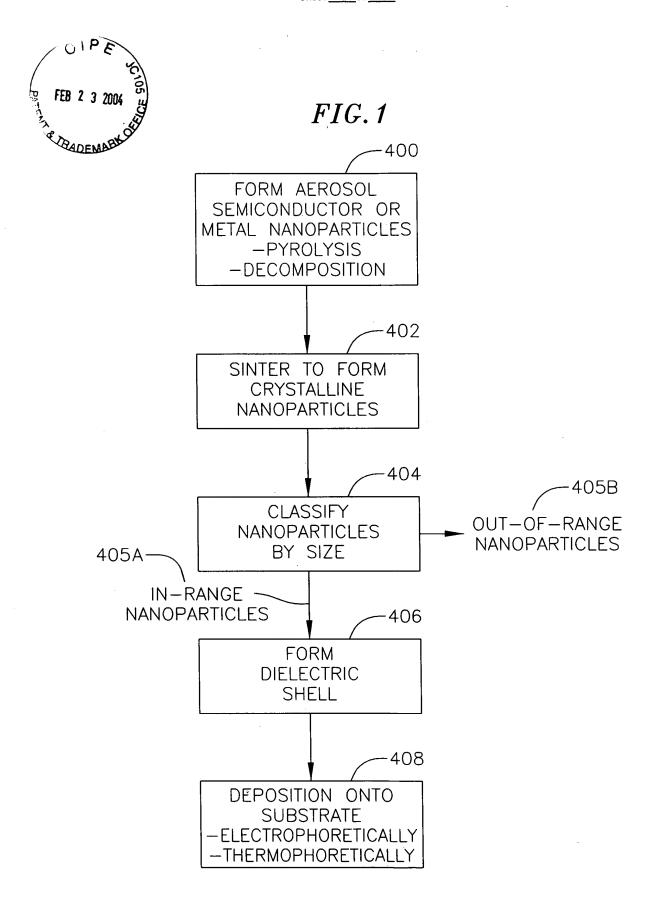
Inventor(s): Richard C. Flagan et al.

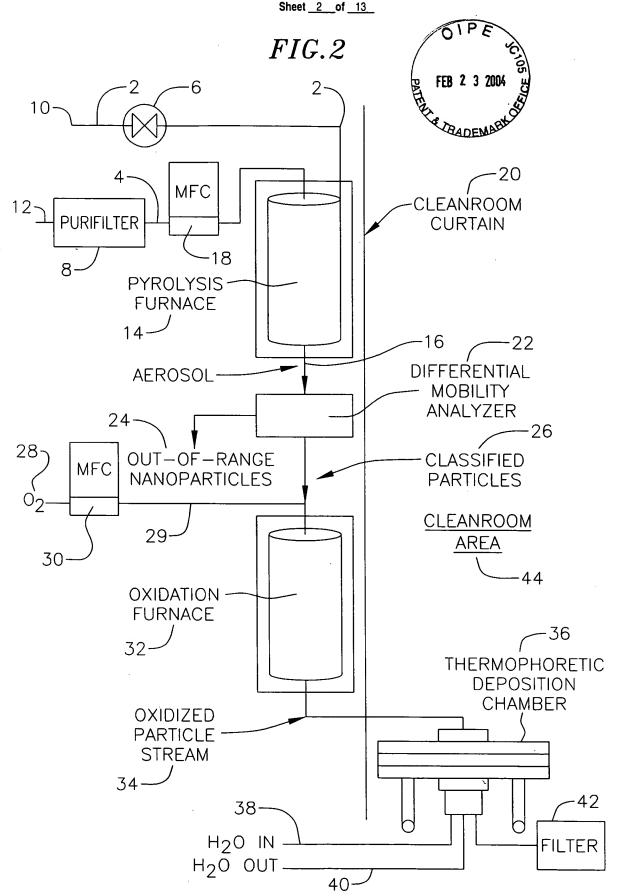
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inventor(s): Richard C. Flagan et al.

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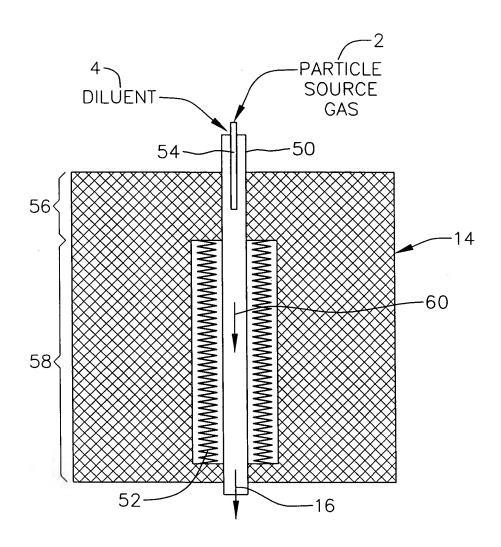


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Inventor(s): Richard C. Flagan et al.

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*FIG.3* 

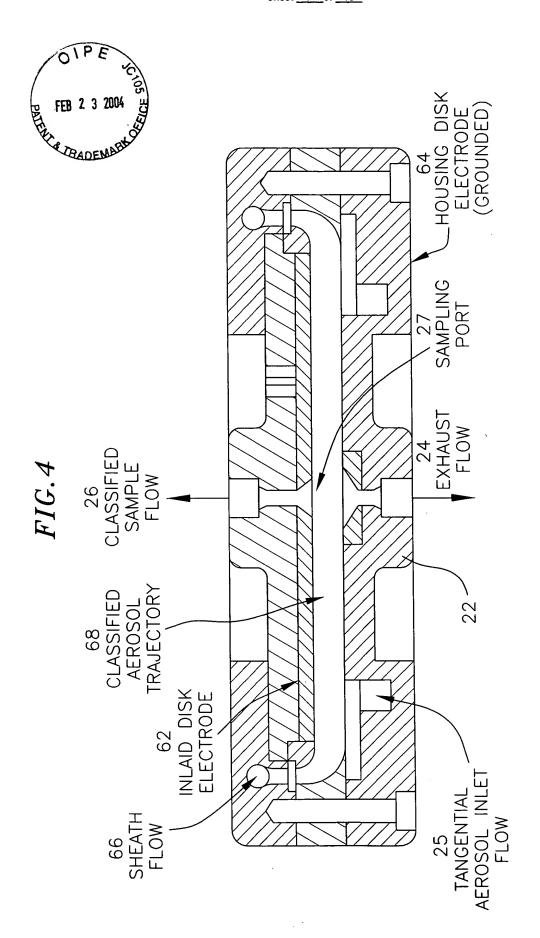


Inventor(s): Richard C. Flagan et al.

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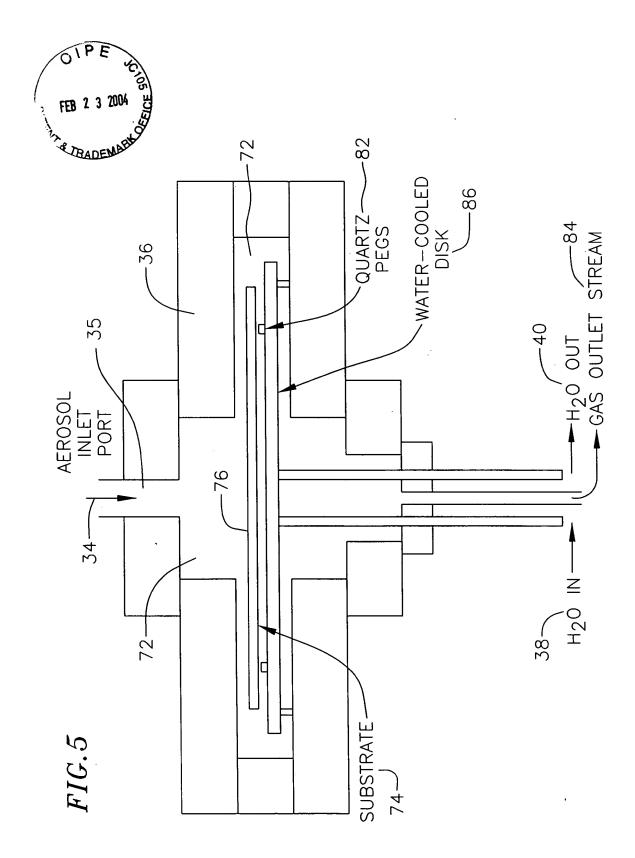
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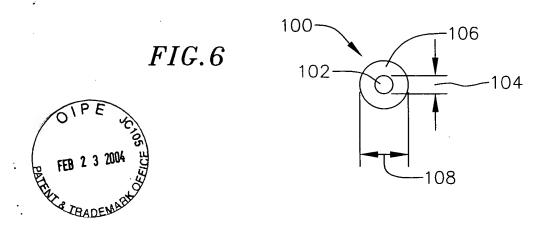
Application No. 09/895,791; Filed: 06/29/2001
Inventor(s): Richard C. Flagan et al.

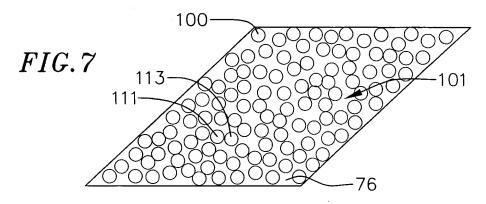
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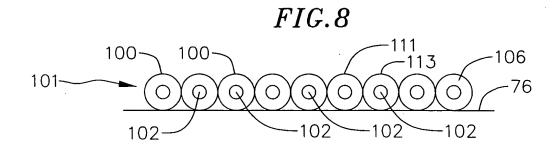


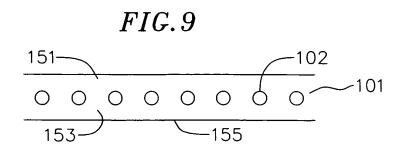
Application No. 09/895,791; Filed: 06/29/2001
Inventor(s): Richard C. Flagan et al.

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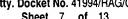






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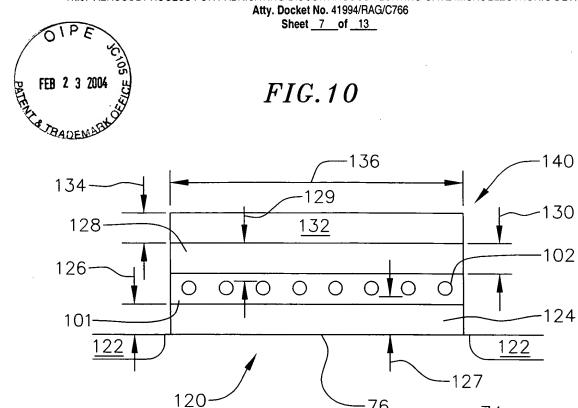
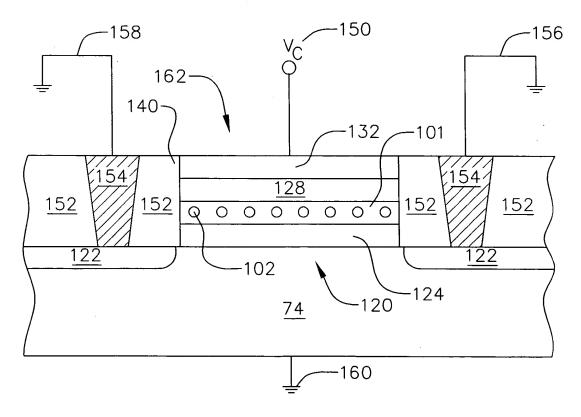


FIG. 11

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<u>74</u>

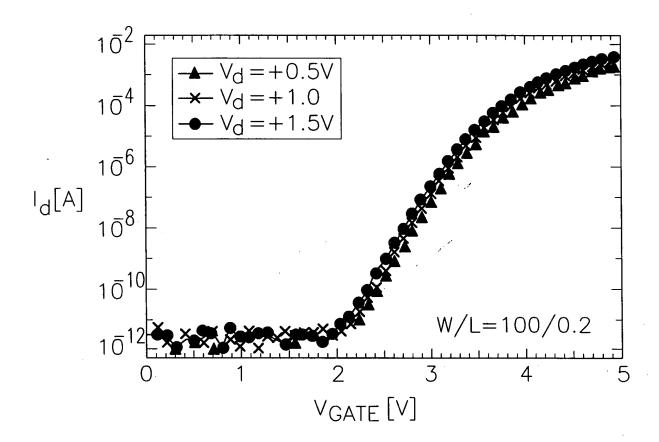


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FIG. 12



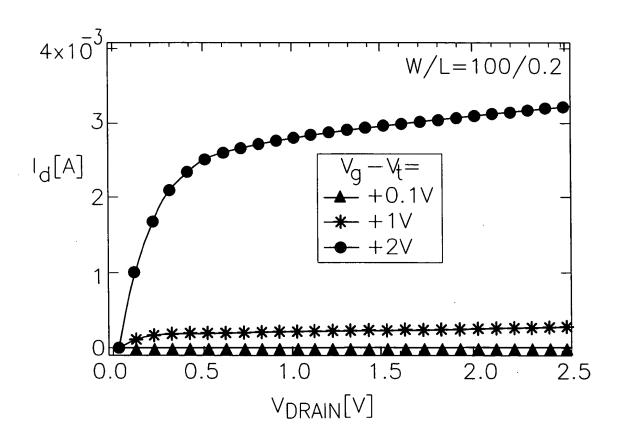
SUBTHRESHOLD CHARACTERISTICS OF A 0.2  $\mu$ m n-TYPE AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET (SUBTHRESHOLD SLOPE=200mV/dec; DIBL=100mV/V).

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FIG. 13



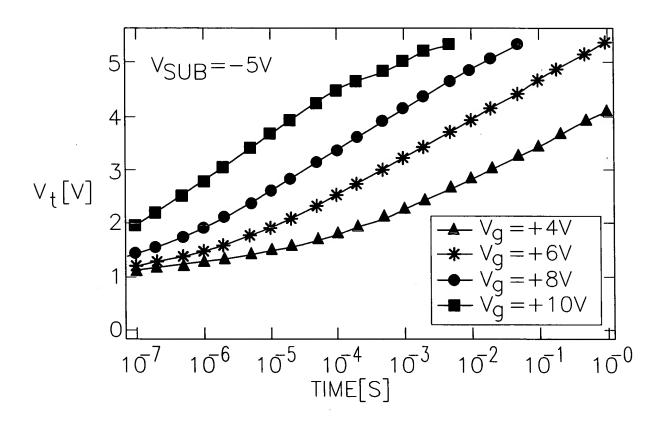
OUTPUT CHARACTERISTICS OF A 0.2  $\mu$ m AEROSOL-NANOCRYSTAL FLOATING-GATE MOSFET; DRIVE CURRENT =  $30\mu$ A/ $\mu$ m

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FIG. 14



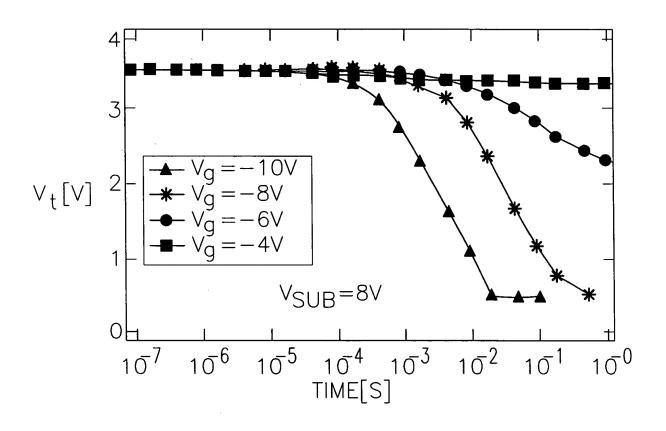
PROGRAMMING TRANSIENTS (UNIFORM FN TUNNELING) OF THE NANOCRYSTAL NVM DEVICE.

Application No. 09/895,791; Filed: 06/29/2001
Inventor(s): Richard C. Flagan et al.

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FIG. 15



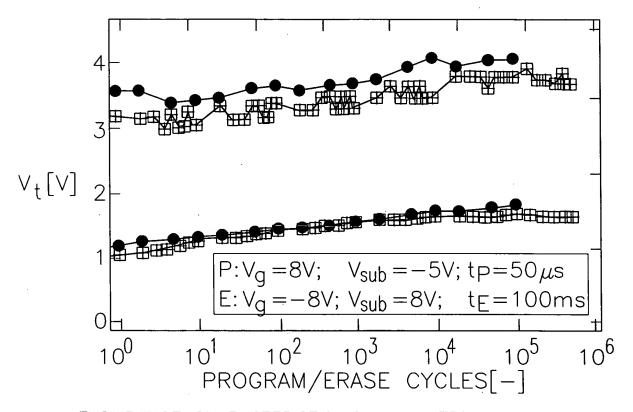
ERASE TRANSIENTS (UNIFORM FN TUNNELING).

Application No. 09/895,791; Filed: 06/29/2001
Inventor(s): Richard C. Flagan et al.

Title: AEROSOL PROCESS FOR FABRICATING DISCONTINUOUS FLOATING GATE MICROELECTRONIC DEVICES
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FIG. 16



ENDURANCE CHARACTERISTIC; ONLY LIMITED WINDOW CLOSURE IS OBSERVED AFTER 10<sup>5</sup> PROGRAM/ERASE CYCLES.



FIG. 17

